



Bipolar PNP Bare Die – BTP6324

Part Description

The BTP6324 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. NPN complement is BTN6324

Key Parameters:

- VCBO = -80V
- VCEO = -80V
- VEBO = -8V
- hFE = 56-390 @ VCE = -10V, IC = -0.15A
- VCE(Sat) = -0.4V @ IC = -0.5A, IB = -50mA
- fT = 200 MHz @ VCE = -10V, IE = 0A
- COBO = 20pF @ VCB = -10V

Features

Low VCE(sat). Designed to provide performance equivalent to ROHM 2SA935

Die Size (Unawn)

700µm X 700µm, 28 Mils X 28 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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